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Integrated Dual RF Receiver

Preliminary Technical Data ADRV9008-1

FEATURES

Dual receivers Maximum receiver bandwidth: 200 MHz Fully integrated, fractional-N, RF synthesizers Fully integrated clock synthesizer Multichip phase synchronization for RF LO and baseband clocks JESD204B datapath interface Tuneable range: 75 MHz to 6000 MHz

APPLICATIONS

3G/4G/5G FDD, macrocell base stations Wideband active antenna systems Massive multiple input, multiple output (MIMO) Phased array radar Electronic warfare Military communications Portable test equipment

GENERAL DESCRIPTION

The ADRV9008-1 is a highly integrated, dual radio frequency (RF), agile receiver (Rx) offering integrated synthesizers and digital signal processing functions. The IC delivers a versatile combination of high performance and low power consumption required by 3G/4G/5G macrocell, frequency division duplex (FDD), base station applications.

The receive path consists of two independent, wide bandwidth, direct conversion receivers with state-of-the-art dynamic range. The complete receive subsystem includes automatic and manual attenuation control, dc offset correction, quadrature error correction (QEC), and digital filtering, eliminating the need for these functions in the digital baseband. RF front-end control and several auxiliary functions such as analog-to-digital converters (ADCs), digital-to-analog converters (DACs), and general-purpose input/outputs (GPIOs) for the power amplifier (PA) are also integrated.

In addition to automatic gain control (AGC), the ADRV9008-1 also features flexible external gain control modes, allowing significant flexibility in setting system level gain dynamically.

The received signals are digitized with a set of four, high dynamic range, continuous time, sigma-delta (Σ - Δ) ADCs that provide inherent antialiasing. The combination of the direct conversion architecture (which does not suffer from out of band image mixing) and the lack of aliasing relaxes the requirements of the RF filters compared to the requirements of traditional intermediate frequency (IF) receivers.

The fully integrated phase-locked loop (PLL) provides high performance, low power, fractional-N, RF synthesis for the receiver signal paths. An additional synthesizer generates the clocks needed for the converters, digital circuits, and serial interface. A multichip synchronization mechanism synchronizes the phase of the RF local oscillator (LO) and baseband clocks between multiple ADRV9008-1 chips. The ADRV9008-1 has the isolation that high performance base station applications require. All voltage controlled oscillators (VCOs) and loop filter components are integrated.

The high speed JESD204B interface supports up to 12.288 Gbps lane rates, resulting in a single lane per receiver in the widest bandwidth mode. The interface also supports interleaved mode for lower bandwidths, reducing the total number of high speed data interface lanes to one. Both fixed and floating point data formats are supported. The floating point format allows internal AGC to be invisible to the demodulator device.

The core of the ADRV9008-1 can be powered directly from 1.3 V and 1.8 V regulators and is controlled via a standard 4-wire serial port. Comprehensive power-down modes are included to minimize power consumption during normal use. The ADRV9008-1 is packaged in a 12 mm \times 12 mm, 196-ball chip scale ball grid array (CSP_BGA).

Rev. PrA Document Feedback

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SPECIFICATIONS

Electrical characteristics at VDDA1P3¹ = 1.3 V, VDDD1P3_DIG = 1.3 V, T_J = full operating temperature range. LO frequency (f_{LO}) = 1800 MHz, unless otherwise noted. The specifications in Table 1 are not deembedded. Refer to the Typical Performance Characteristics section for input/output circuit path loss. The device configuration profile, unless otherwise specified, is as follows: receiver = 200 MHz (IQ rate = 245.76 MHz), JESD204B rate = 9.8304 GSPS, and device clock = 245.76 MHz. **Table 1.**

ADRV9008-1 Preliminary Technical Data

¹ VDDA1P3 refers to all analog 1.3 V supplies, including VDDA1P3_RF_SYNTH, VDDA1P3_BB, VDDA1P3_RX_RF, VDDA1P3_RF_VCO_LDO, VDDA1P3_RF_LO, VDDA1P3_DES, VDDA1P3_SER, VDDA1P3_CLOCK_SYNTH, VDDA1P3_CLOCK_VCO_LDO, VDDA1P3_AUX_SYNTH, and VDDA1P3_AUX_VCO_LDO.

CURRENT AND POWER CONSUMPTION SPECIFICATIONS

¹ VDDA1P3 refers to all analog 1.3 V supplies, including VDDA1P3_RF_SYNTH, VDDA1P3_BB, VDDA1P3_RX_RF, VDDA1P3_RX, VDDA1P3_RF_VCO_LDO, VDDA1P3_RF_LO, VDDA1P3_DES, VDDA1P3_SER, VDDA1P3_CLOCK_SYNTH, VDDA1P3_CLOCK_VCO_LDO, VDDA1P3_AUX_SYNTH, and VDDA1P3_AUX_VCO_LDO.

TIMING DIAGRAMS

Figure 3. SYSREF_IN± Setup and Hold Timing Examples, Relative to Device Clock

ABSOLUTE MAXIMUM RATINGS

Table 3.

¹ VDDA1P3 refers to all analog 1.3 V supplies, including VDDA1P3_RF_SYNTH, VDDA1P3_BB, VDDA1P3_RX_RF, VDDA1P3_RX, VDDA1P3_RF_VCO_LDO, VDDA1P3_RF_LO, VDDA1P3_CLOCK_SYNTH, VDDA1P3_RX_LO_BUFFER, and VDDA1P3_CLOCK.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

REFLOW PROFILE

The ADRV9008-1 reflow profile is in accordance with the JEDEC JESD204B criteria for Pb-free devices. The maximum reflow temperature is 260°C.

THERMAL MANAGEMENT

The ADRV9008-1 is a high power device that can dissipate over 3 W depending on the user application and configuration. Because of the power dissipation, the ADRV9008-1 uses an

exposed die package to provide the customer with the most effective method of controlling the die temperature. The exposed die allows cooling of the die directly. Figure 4 shows the profile view of the device mounted to a user printed circuit board (PCB) and a heat sink (typically the aluminum case) to keep the junction (exposed die) below the maximum junction temperature shown in Table 3. The device is designed for a lifetime of 10 years when operating at the maximum junction temperature.

THERMAL RESISTANCE

 θ_{IA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages. Thermal resistance data for the ADRV9008-1 mounted on both a JEDEC 2S2P test board and a 10-layer Analog Devices, Inc., evaluation board are listed in Table 4. Do not exceed the absolute maximum junction temperature rating in Table 3. 10-layer PCB entries refer to the 10-layer Analog Devices evaluation board, which more accurately reflects the PCB used in customer applications.

Table 4. Thermal Resistance1, 2

¹ For the θ_{JC} test, 100 µm thermal interface material (TIM) is used. TIM is assumed to have 3.6 thermal conductivity watts/(meter \times Kelvin).

² Using enhanced heat removal techniques such as PCB, heat sink, and airflow improves the thermal resistance values.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Figure 4. Typical Thermal Management Solution

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

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Figure 5. Pin Configuration

Table 5. Pin Function Descriptions

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TYPICAL PERFORMANCE CHARACTERISTICS

The temperature settings refer to the die temperature.

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650 MHz TO 3000 MHz BAND

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